

Product Summary

$V_{(BR)DSS}$	$R_{DS(on)}$	I_D $T_A = +25^\circ\text{C}$
-50V	6Ω @ $V_{GS} = -4\text{V}$	-160mA
	8Ω @ $V_{GS} = -2.5\text{V}$	-120mA

Descriptions and Applications

This new generation MOSFET is designed to minimize the on-state resistance ($R_{DS(on)}$) and yet maintain superior switching performance, making it ideal for high-efficiency power management applications.

- DC-DC Converters
- Power Management Functions
- Battery Operated Systems and Solid-State Relays

Features and Benefits

- Low On-Resistance
- ESD Protected Gate
- Low Input Capacitance
- Fast Switching Speed
- **Lead-Free Finish; RoHS Compliant (Notes 1 & 2)**
- **Halogen and Antimony Free. "Green" Device (Note 3)**
- **For automotive applications requiring specific change control (i.e. parts qualified to AEC-Q100/101/200, PPAP capable, and manufactured in IATF 16949 certified facilities), please [contact us](#) or your local Diodes representative.**

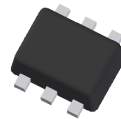
<https://www.diodes.com/quality/product-definitions/>

Mechanical Data

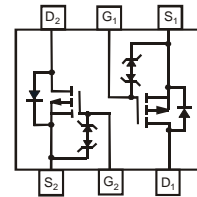
- Package: SOT563
- Package Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020D
- Terminals: Finish — Matte Tin annealed over Copper Leadframe. Solderable per MIL-STD-202, Method 208 (e3)
- Weight: 0.006 grams (Approximate)



SOT563



TOP VIEW



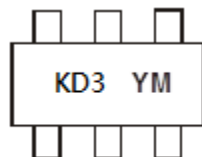
TOP VIEW
Internal Schematic

Ordering Information (Note 4)

Part Number	Package	Packing	
		Qty.	Carrier
DMP56D0UV -7	SOT563	3000	Tape & Reel
DMP56D0UV -13	SOT563	10000	Tape & Reel

- Notes:
1. EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant. All applicable RoHS exemptions applied.
 2. See <https://www.diodes.com/quality/lead-free/> for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
 4. For packaging details, go to our website at <https://www.diodes.com/design/support/packaging/diodes-packaging/>.

Marking Information



KD3 = Product Type Marking Code
 YM = Date Code Marking
 Y = Year (ex: H = 2021)
 M = Month (ex: 9 = September)

Date Code Key

Year	2008	2021	2022	2023	2024	2025	2026	2027	2028	2029	2030
Code	V	I	J	K	L	M	N	O	P	R	S

Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	O	N	D

Maximum Ratings (@ $T_A = +25^\circ\text{C}$, unless otherwise specified.)

Characteristic	Symbol	Value	Units
Drain-Source Voltage	V_{DSS}	-50	V
Gate-Source Voltage	V_{GSS}	± 8	V
Drain Current (Note 5)	I_D	-160	mA
Pulsed Drain Current (10 μs pulse, duty cycle = 1%)	I_{DM}	-700	mA

Thermal Characteristics (@ $T_A = +25^\circ\text{C}$, unless otherwise specified.)

Characteristic	Symbol	Value	Units
Total Power Dissipation (Note 5)	P_D	400	mW
Thermal Resistance, Junction to Ambient (Note 5)	$R_{\theta JA}$	313	$^\circ\text{C/W}$
Operating and Storage Temperature Range	T_J, T_{STG}	-55 to +150	$^\circ\text{C}$

Electrical Characteristics (@ $T_A = +25^\circ\text{C}$, unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 6)						
Drain-Source Breakdown Voltage	BV_{DSS}	-50	—	—	V	$V_{GS} = 0V, I_D = -250\mu\text{A}$
Zero Gate Voltage Drain Current	I_{DSS}	—	—	-10	μA	$V_{DS} = -50V, V_{GS} = 0V$
Gate-Body Leakage	I_{GSS}	—	—	± 1	μA	$V_{GS} = \pm 8V, V_{DS} = 0V$
ON CHARACTERISTICS (Note 6)						
Gate Threshold Voltage	$V_{GS(th)}$	-0.5	—	-1.2	V	$V_{DS} = V_{GS}, I_D = -250\mu\text{A}$
Static Drain-Source On-Resistance	$R_{DS(on)}$	—	4.6 6.0	6 8	Ω	$V_{GS} = -4V, I_D = -100\text{mA}$ $V_{GS} = -2.5V, I_D = -80\text{mA}$
Forward Transfer Admittance	$ Y_{fs} $	100	—	—	mS	$V_{DS} = -5V, I_D = -100\text{mA}$
Diode Forward Voltage	V_{SD}	—	-0.8	-1.2	V	$V_{GS} = 0V, I_S = -100\text{mA}$
DYNAMIC CHARACTERISTICS (Note 7)						
Input Capacitance	C_{iss}	—	50.54	—	pF	$V_{DS} = -25V, V_{GS} = 0V, f = 1.0\text{MHz}$
Output Capacitance	C_{oss}	—	3.49	—	pF	
Reverse Transfer Capacitance	C_{rss}	—	2.42	—	pF	
Gate Resistance	R_G	—	201	—	Ω	$V_{DS} = 0V, V_{GS} = 0V, f = 1.0\text{MHz}$
Total Gate Charge $V_{GS} = 4.5V$	Q_g	—	0.58	—	nC	$V_{DS} = -25V, I_D = -100\text{mA}$
Gate-Source Charge	Q_{gs}	—	0.09	—	nC	
Gate-Drain Charge	Q_{gd}	—	0.14	—	nC	
Turn-On Delay Time	$t_{D(on)}$	—	4.46	—	nS	$V_{DD} = -30V, I_D = -0.27A, V_{GEN} = -4V, R_{GEN} = 6\Omega$
Turn-On Rise Time	t_r	—	6.63	—	nS	
Turn-Off Delay Time	$t_{D(off)}$	—	21.9	—	nS	
Turn-Off Fall Time	t_f	—	15.0	—	nS	

- Notes:
5. Device mounted on FR-4 PC board, with minimum recommended pad layout, single sided.
 6. Short duration pulse test used to minimize self-heating effect.
 7. Guaranteed by design. Not subject to production testing.

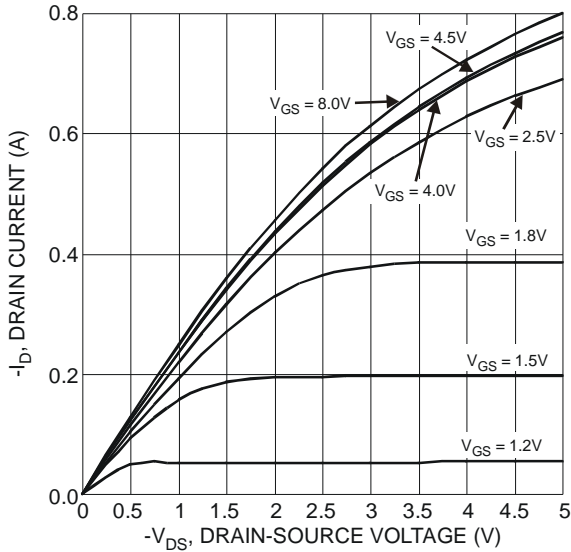


Figure 1 Typical Output Characteristics

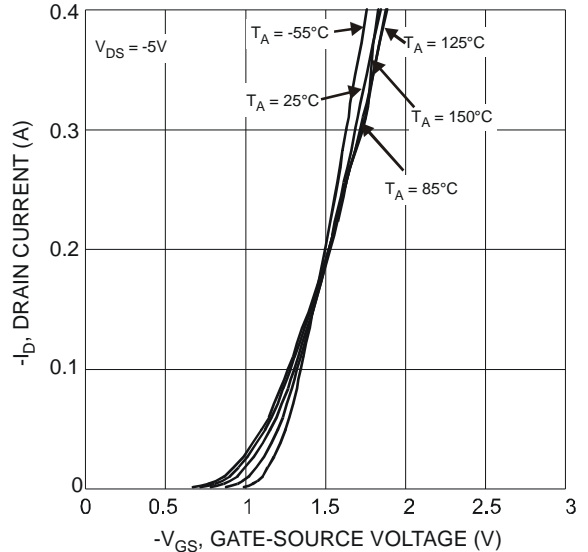


Figure 2 Typical Transfer Characteristics

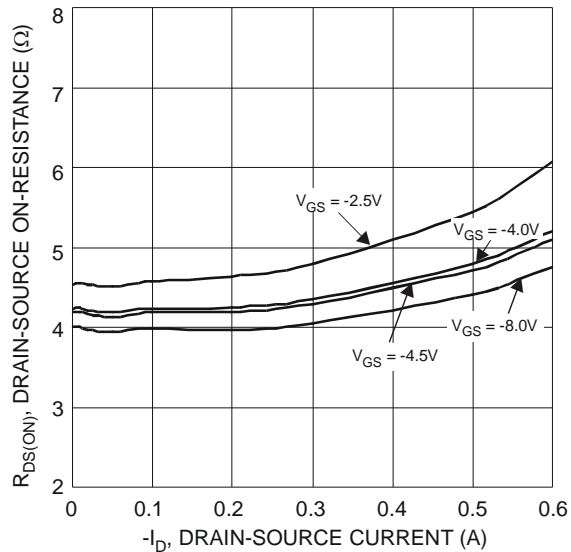


Figure 3 Typical On-Resistance vs. Drain Current and Gate Voltage

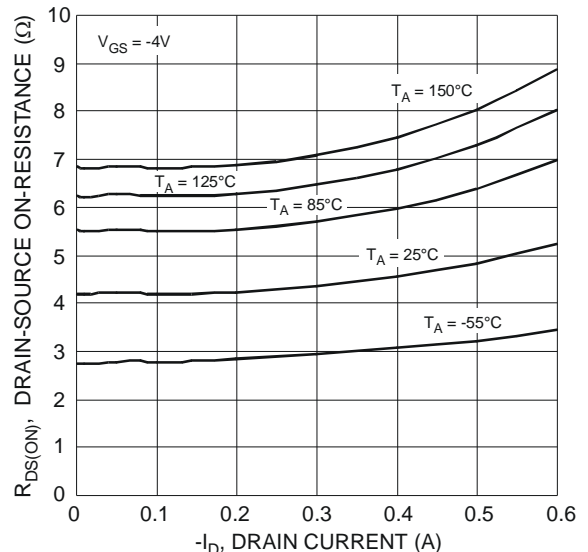


Figure 4 Typical On-Resistance vs. Drain Current and Temperature

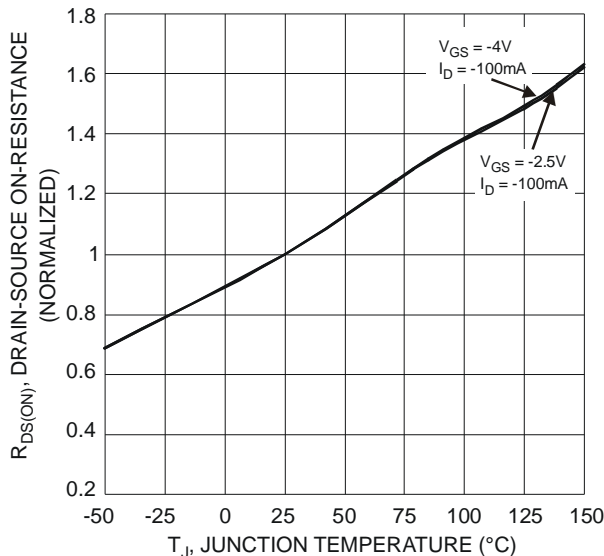


Figure 5 On-Resistance Variation with Temperature

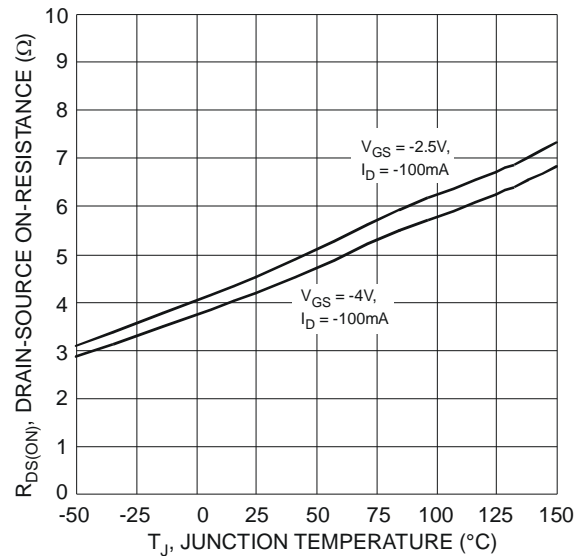


Figure 6 On-Resistance Variation with Temperature

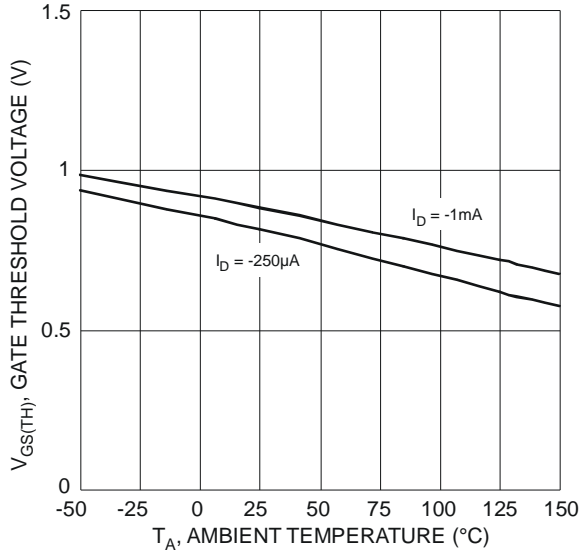


Figure 7 Gate Threshold Variation vs. Ambient Temperature

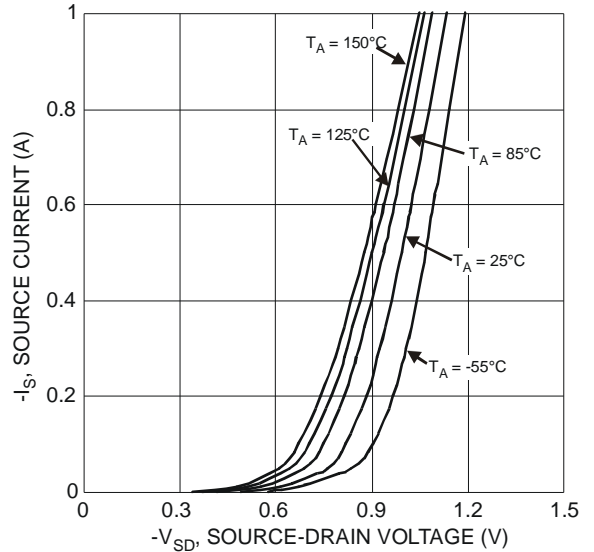


Figure 8 Diode Forward Voltage vs. Current

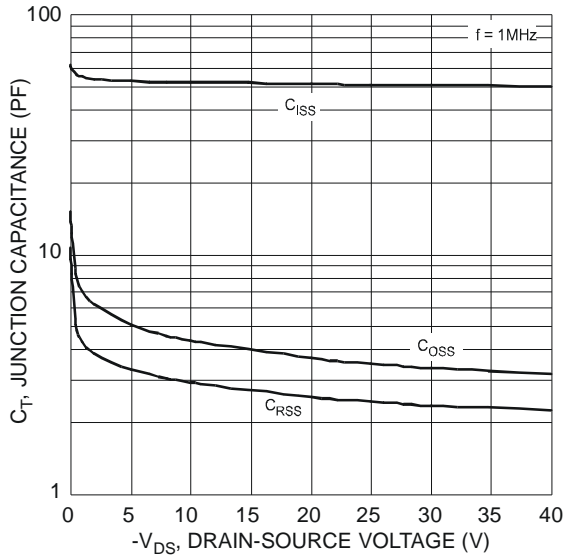


Figure 9 Typical Junction Capacitance

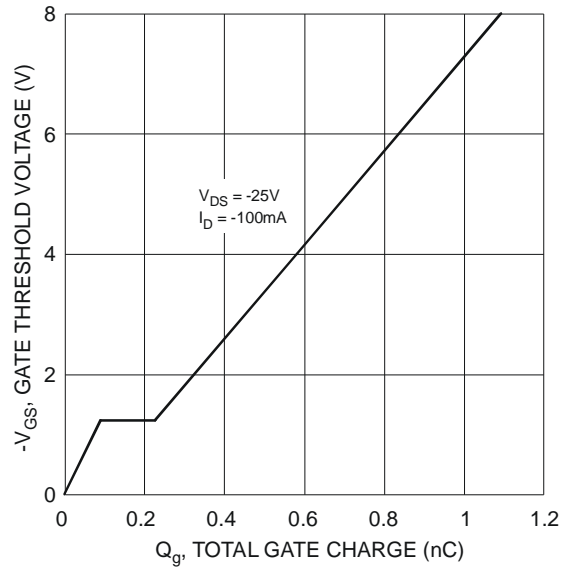
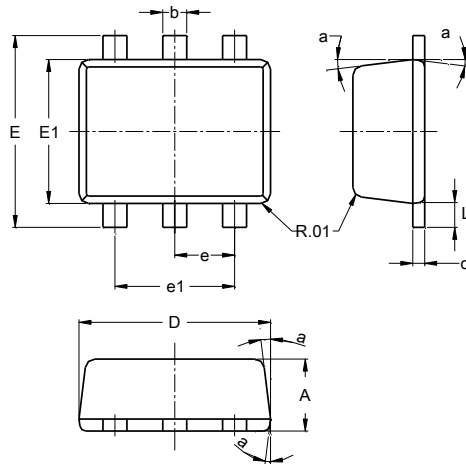


Figure 10 Gate Charge Characteristics

Package Outline Dimensions

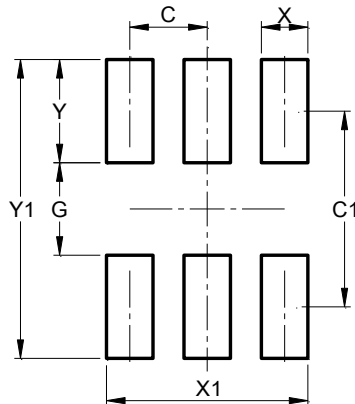
Please see <http://www.diodes.com/package-outlines.html> for the latest version.



SOT563			
Dim	Min	Max	Typ
A	0.55	0.60	--
b	0.15	0.30	0.20
c	0.10	0.18	0.11
D	1.50	1.70	1.60
E	1.55	1.70	1.60
E1	1.10	1.25	1.20
e	--	--	0.50
e1	0.90	1.10	1.00
L	0.10	0.30	0.20
a	8°	9°	7°
All Dimensions in mm			

Suggested Pad Layout

Please see <http://www.diodes.com/package-outlines.html> for the latest version.



Dimensions	Value (in mm)
C	0.500
C1	1.270
G	0.600
X	0.300
X1	1.300
Y	0.670
Y1	1.940

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